

**Features:**

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V <sub>RRM</sub> , V <sub>DRM</sub>	Type & Outline		
	MTx200-26-413F3	MFx200-26-413F3	MTx200-28-413F3
2600V	MTx200-28-413F3	MFx200-28-413F3	MFx200-30-413F3
3000V	MTx200-30-413F3	MFx200-30-413F3	MFx200-32-413F3
3200V	MTx200-32-413F3	MFx200-32-413F3	MFx200-34-413F3
3400V	MTx200-34-413F3	MFx200-34-413F3	MFx200-36-413F3
3600V	MTx200-36-413F3	MFx200-36-413F3	MFx200-36-413F3G
3600V	MT200-36-413F3G		

MTx stands for any type of **MTC**, **MTA**, **MTK**  
MFx stands for any type of **MFC**, **MFA**, **MFK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT	
				Min	Type	Max		
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Single side cooled, T <sub>c</sub> =85°C	125			200	A	
I <sub>T(RMS)</sub>	RMS on-state current					314	A	
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			40	mA	
I <sub>TSM</sub>	Surge on-state current			125		6	kA	
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination	V <sub>R</sub> =60%V <sub>RRM</sub> , t=10ms half sine	125			180	10 <sup>3</sup> A <sup>2</sup> s	
V <sub>TO</sub>	Threshold voltage			125		0.96	V	
r <sub>T</sub>	On-state slope resistance					1.30	mΩ	
V <sub>TM</sub>	Peak on-state voltage			25		2.55	V	
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			1000	V/μs	
di/dt	Critical rate of rise of on-state current			125		200	A/μs	
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	30		180	mA	
V <sub>GT</sub>	Gate trigger voltage			0.8		2.5	V	
I <sub>H</sub>	Holding current			10		200	mA	
I <sub>L</sub>	Latching current					1000	mA	
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.20	V	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case					0.12	°C/W	
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink					0.04	°C/W	
V <sub>iso</sub>	Isolation voltage				4000		V	
F <sub>m</sub>	Terminal connection torque(M8)				10		N·m	
	Mounting torque(M6)				4.5		N·m	
T <sub>vj</sub>	Junction temperature				-40		125	°C
T <sub>stg</sub>	Stored temperature				-40		125	°C
W <sub>t</sub>	Weight	413F3			810		g	
Outline								

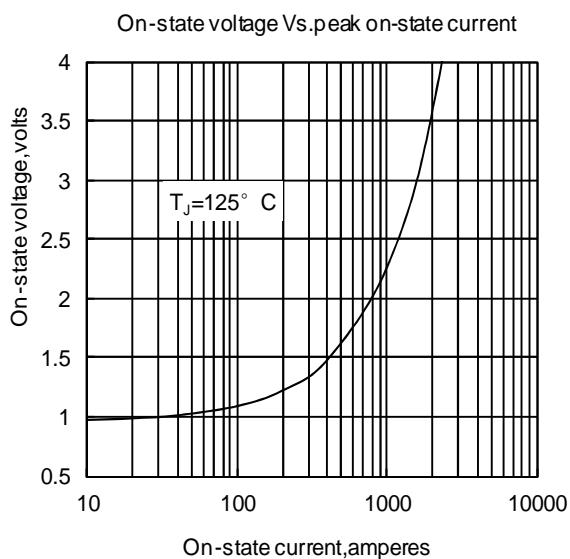


Fig. 1

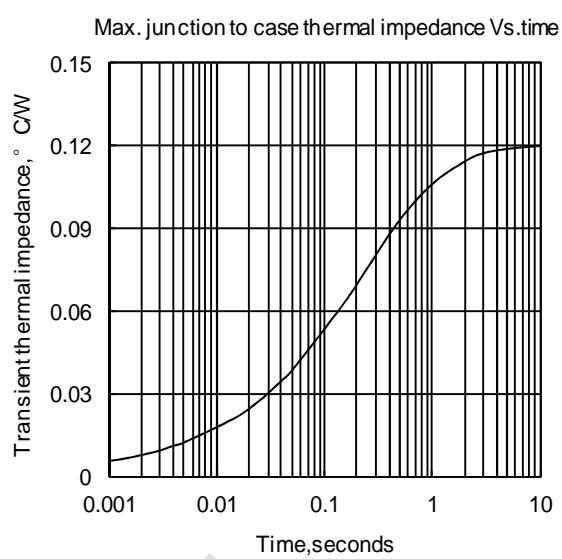


Fig. 2

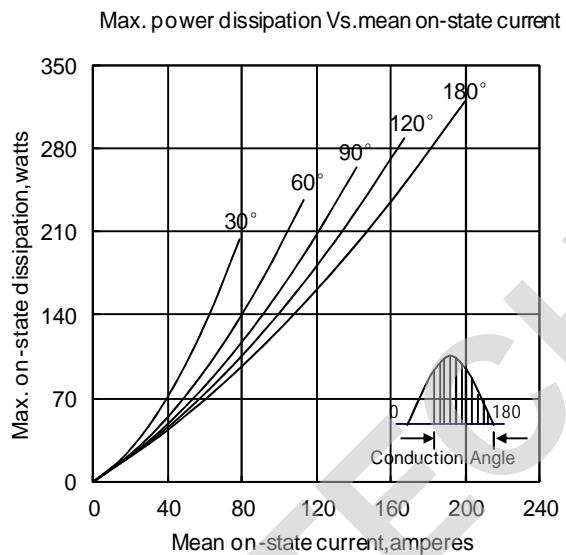


Fig. 3

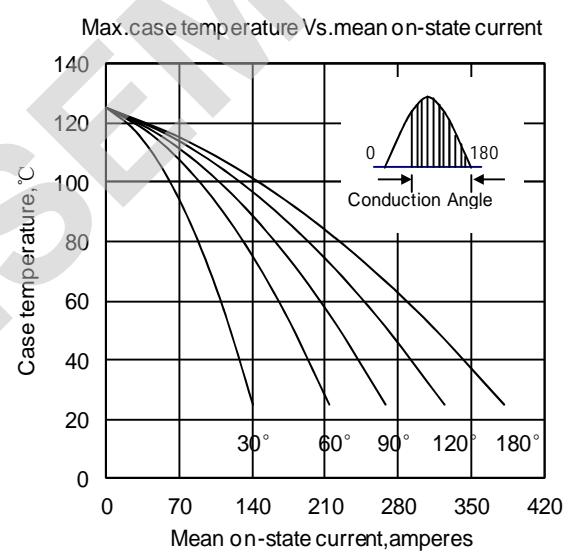


Fig. 4

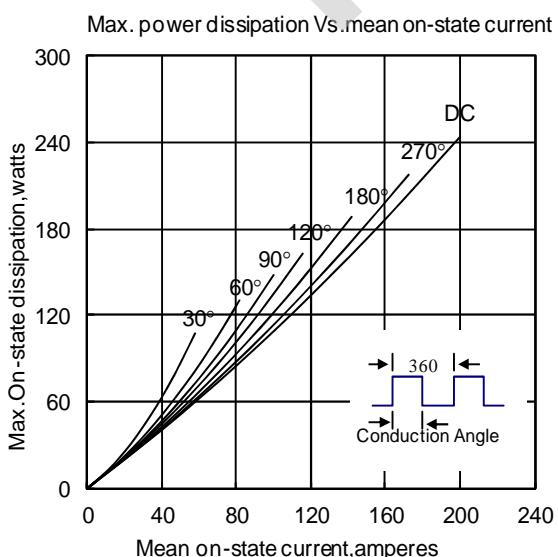


Fig. 5

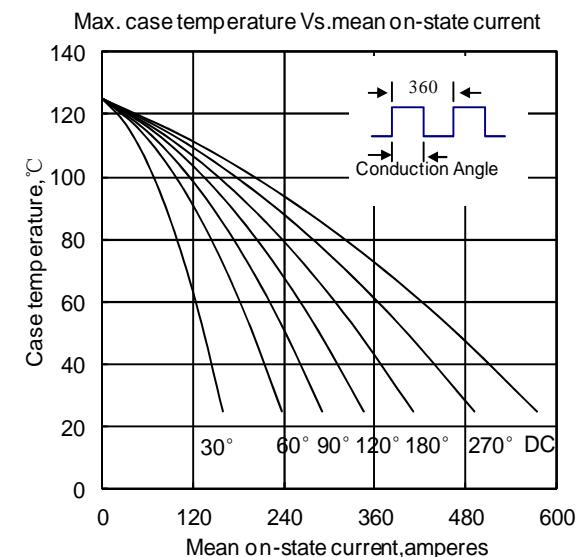


Fig. 6

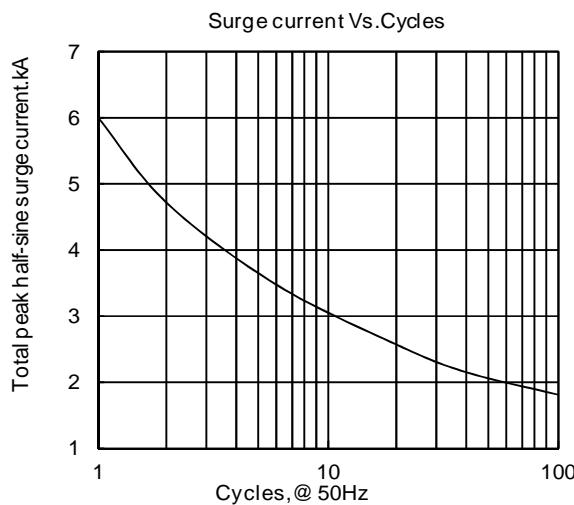


Fig. 7

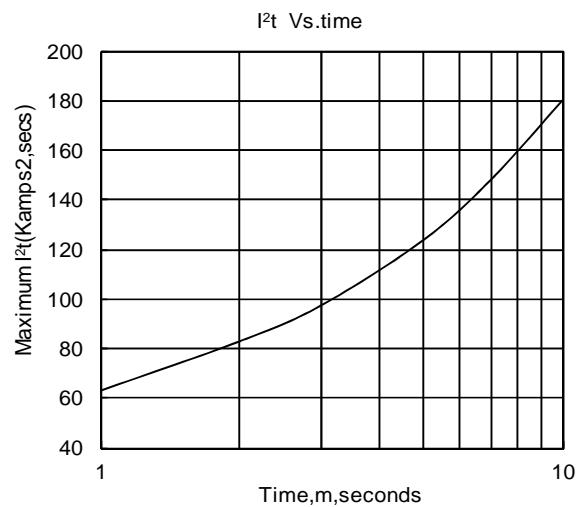


Fig. 8

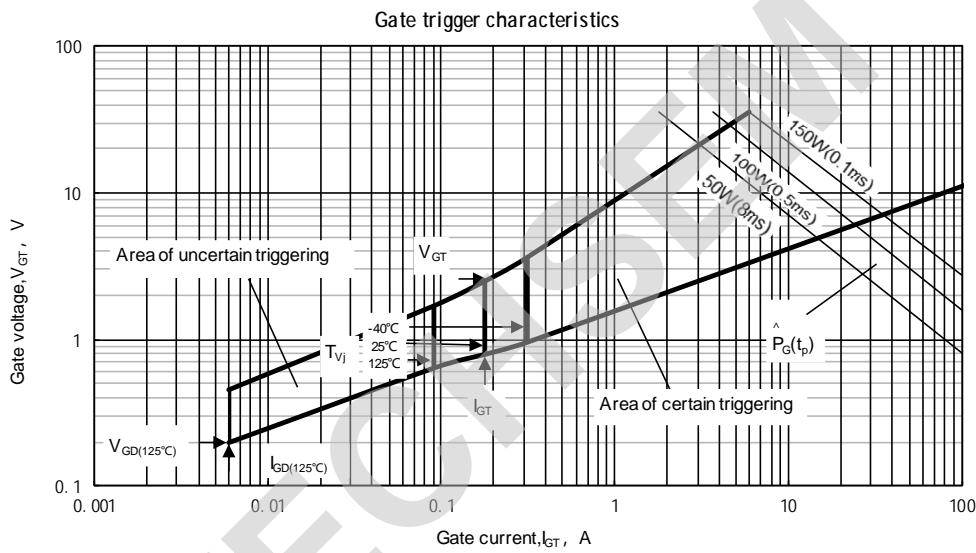
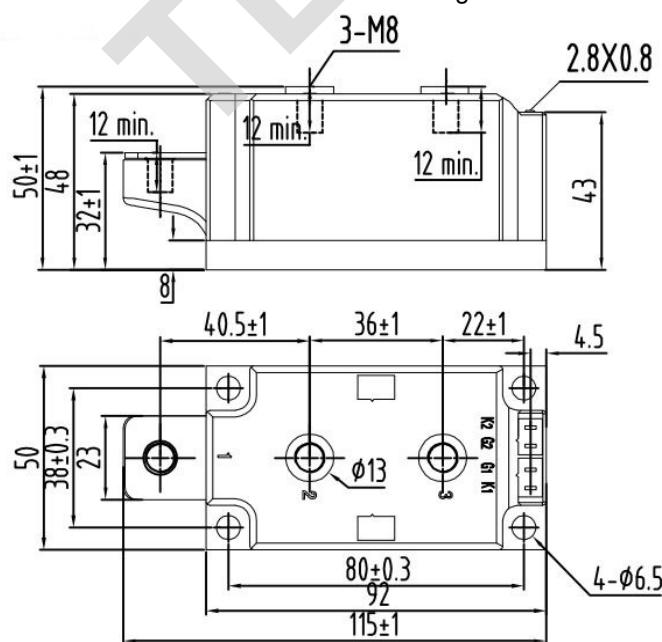


Fig. 9

**Outline:****Unmarked dimensional tolerance: ±0.5mm**

TECHSEM reserves the right to change specifications without notice.